



# PMDXB600UNE

20 V, dual N-channel Trench MOSFET

16 September 2013

Product data sheet

## 1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1010B-6 (SOT1216) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

## 2. Features and benefits

- Trench MOSFET technology
- Leadless ultra small and ultra thin SMD plastic package: 1.1 × 1.0 × 0.37 mm
- Exposed drain pad for excellent thermal conduction
- ElectroStatic Discharge (ESD) protection > 1 kV HBM
- Drain-source on-state resistance  $R_{DSon} = 470 \text{ m}\Omega$

## 3. Applications

- Relay driver
- High-speed line driver
- Low-side load switch
- Switching circuits

## 4. Quick reference data

Table 1. Quick reference data

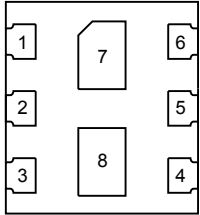
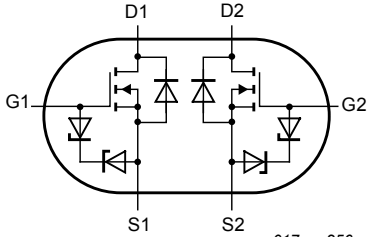
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Per transistor</b>						
$V_{DS}$	drain-source voltage	$T_j = 25 \text{ }^\circ\text{C}$	-	-	20	V
$V_{GS}$	gate-source voltage		-8	-	8	V
$I_D$	drain current	$V_{GS} = 4.5 \text{ V}; T_{amb} = 25 \text{ }^\circ\text{C}$	[1]	-	600	mA
<b>Static characteristics (per transistor)</b>						
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 600 \text{ mA}; T_j = 25 \text{ }^\circ\text{C}$	-	470	620	m $\Omega$

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



### 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1	 <p>Transparent top view <b>DFN1010B-6 (SOT1216)</b></p>	 <p>017aaa256</p>
2	G1	gate TR1		
3	D2	drain TR2		
4	S2	source TR2		
5	G2	gate TR2		
6	D1	drain TR1		
7	D1	drain TR1		
8	D2	drain TR2		

### 6. Ordering information

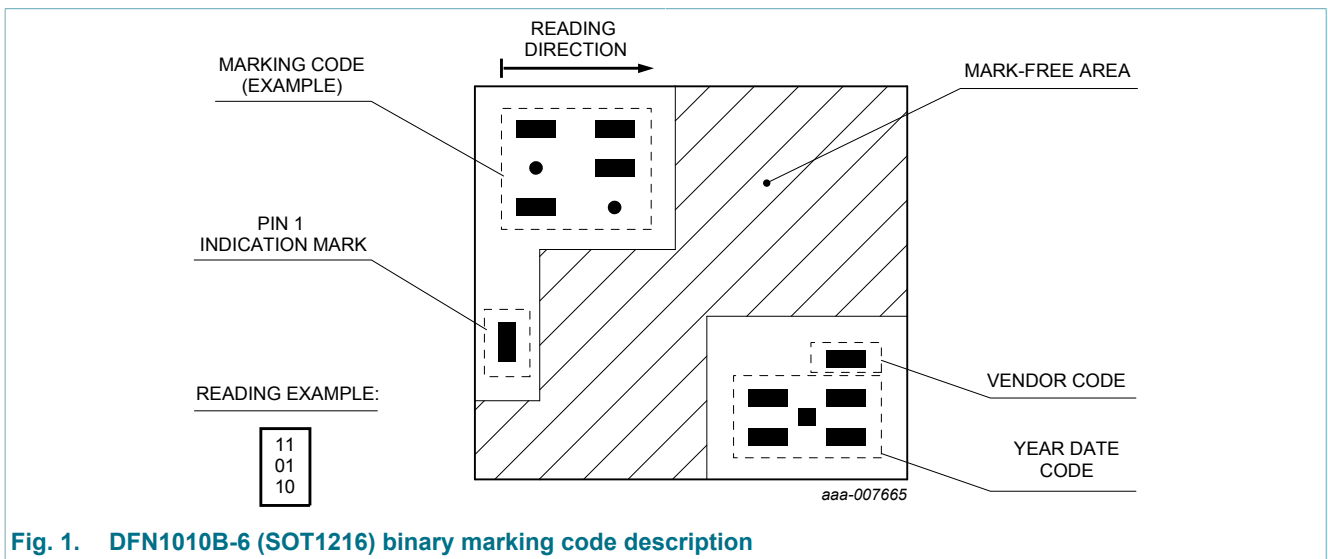
Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMDXB600UNE	DFN1010B-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1216

### 7. Marking

Table 4. Marking codes

Type number	Marking code
PMDXB600UNE	00 10 00



## 8. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
<b>Per transistor</b>						
$V_{DS}$	drain-source voltage	$T_j = 25\text{ °C}$		-	20	V
$V_{GS}$	gate-source voltage			-8	8	V
$I_D$	drain current	$V_{GS} = 4.5\text{ V}; T_{amb} = 25\text{ °C}$	[1]	-	600	mA
		$V_{GS} = 4.5\text{ V}; T_{amb} = 100\text{ °C}$	[1]	-	400	mA
$I_{DM}$	peak drain current	$T_{amb} = 25\text{ °C};$ single pulse; $t_p \leq 10\text{ }\mu\text{s}$		-	2.5	A
$P_{tot}$	total power dissipation	$T_{amb} = 25\text{ °C}$	[2]	-	265	mW
			[1]	-	380	mW
		$T_{sp} = 25\text{ °C}$		-	4025	mW
<b>Source-drain diode</b>						
$I_S$	source current	$T_{amb} = 25\text{ °C}$	[1]	-	0.4	A
<b>Per device</b>						
$T_j$	junction temperature			-55	150	°C
$T_{amb}$	ambient temperature			-55	150	°C
$T_{stg}$	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain  $1\text{ cm}^2$ .

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

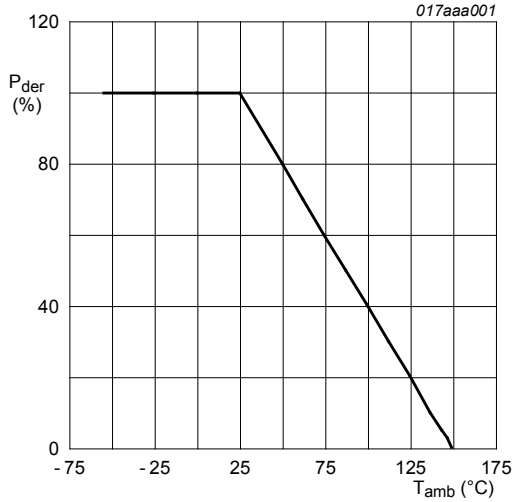


Fig. 2. Normalized total power dissipation as a function of ambient temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ\text{C})}} \times 100\%$$

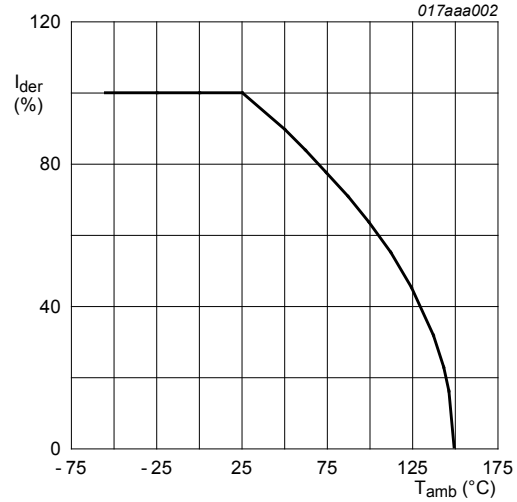
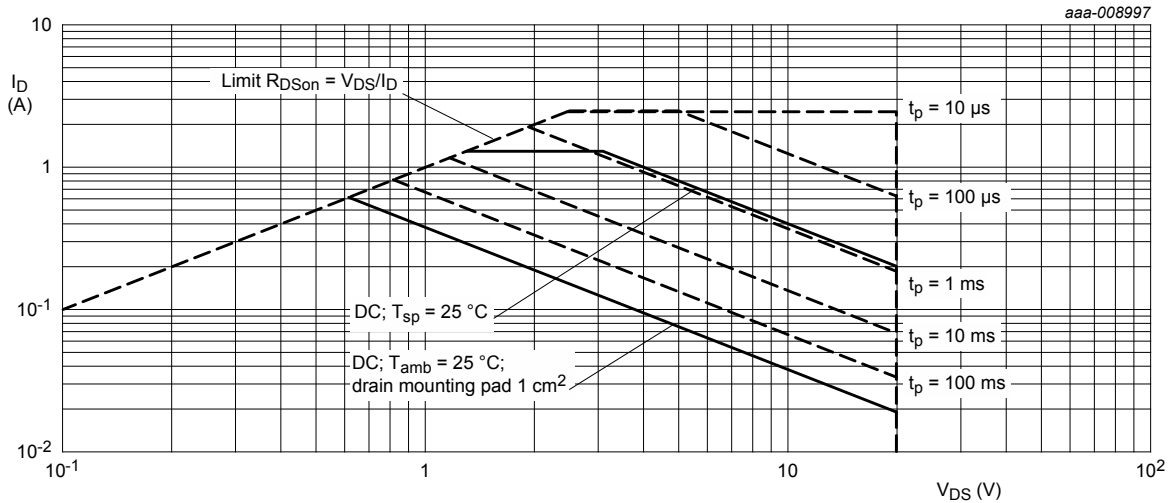


Fig. 3. Normalized continuous drain current as a function of ambient temperature

$$I_{der} = \frac{I_D}{I_{D(25^\circ\text{C})}} \times 100\%$$



$I_{DM}$  = single pulse

Fig. 4. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
<b>Per transistor</b>							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	410	475	K/W
			[2]	-	285	330	K/W

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	27	31	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

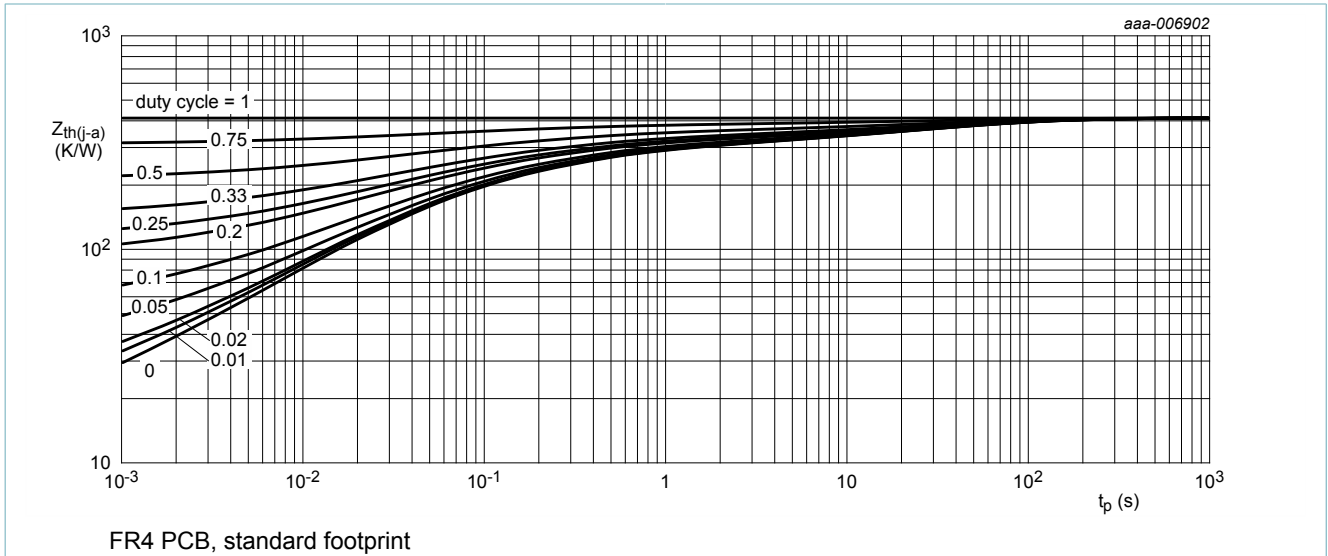


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

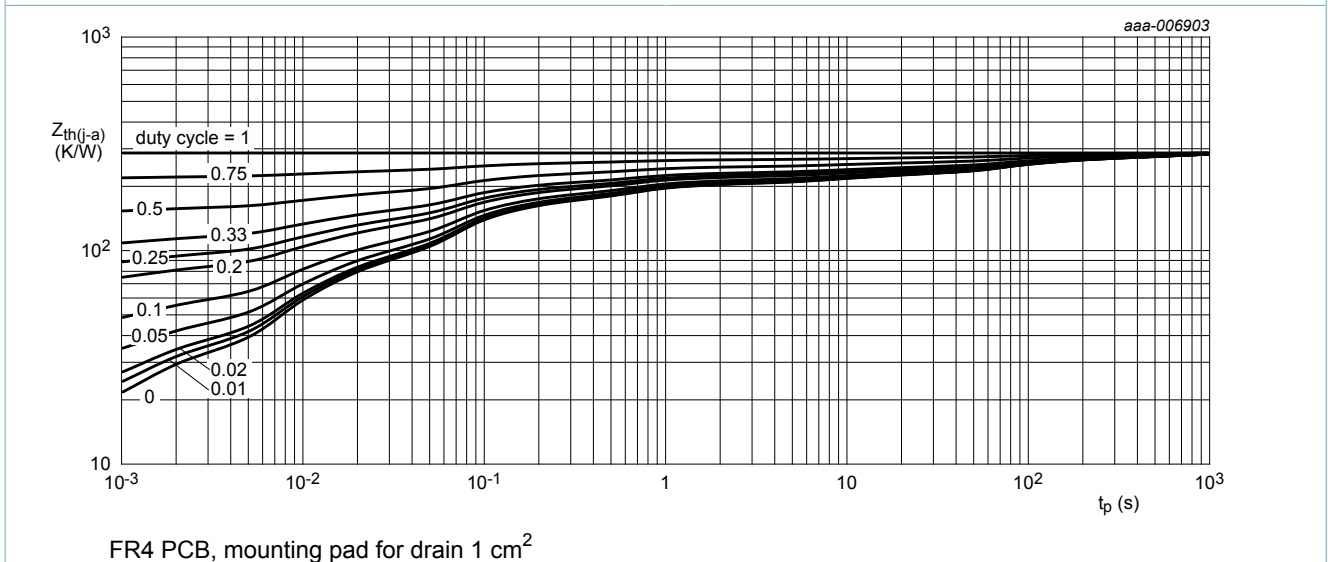
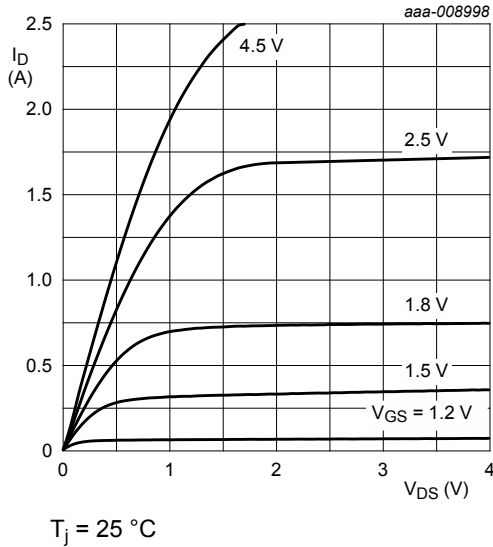


Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

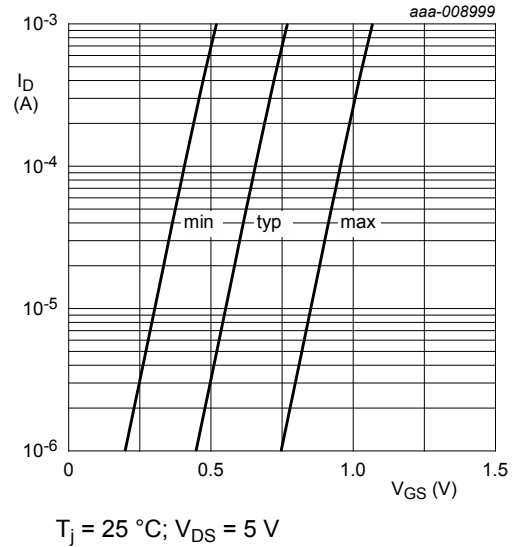
## 10. Characteristics

Table 7. Characteristics

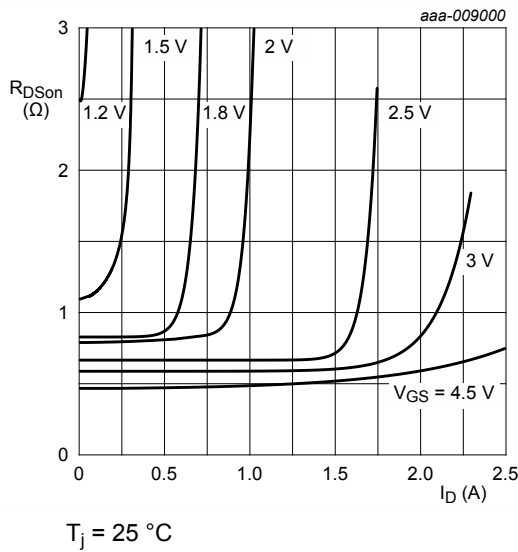
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics (per transistor)</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	20	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C$	0.45	0.7	0.95	V
$I_{DSS}$	drain leakage current	$V_{DS} = 20 V; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	1	$\mu A$
$I_{GSS}$	gate leakage current	$V_{GS} = 8 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	10	$\mu A$
		$V_{GS} = -8 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	-10	$\mu A$
		$V_{GS} = 4.5 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	1	$\mu A$
		$V_{GS} = -4.5 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	-1	$\mu A$
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 4.5 V; I_D = 600 \text{ mA}; T_j = 25 \text{ }^\circ C$	-	470	620	m $\Omega$
		$V_{GS} = 4.5 V; I_D = 600 \text{ mA}; T_j = 150 \text{ }^\circ C$	-	760	1000	m $\Omega$
		$V_{GS} = 2.5 V; I_D = 500 \text{ mA}; T_j = 25 \text{ }^\circ C$	-	620	850	m $\Omega$
		$V_{GS} = 1.8 V; I_D = 100 \text{ mA}; T_j = 25 \text{ }^\circ C$	-	845	1300	m $\Omega$
		$V_{GS} = 1.5 V; I_D = 10 \text{ mA}; T_j = 25 \text{ }^\circ C$	-	1125	3000	m $\Omega$
		$V_{GS} = 1.2 V; I_D = 1 \text{ mA}; T_j = 25 \text{ }^\circ C$	-	2210	-	m $\Omega$
$g_{fs}$	forward transconductance	$V_{DS} = 5 V; I_D = 0.6 \text{ A}; T_j = 25 \text{ }^\circ C$	-	1	-	S
<b>Dynamic characteristics (per transistor)</b>						
$Q_{G(tot)}$	total gate charge	$V_{DS} = 10 V; I_D = 600 \text{ mA}; V_{GS} = 4.5 V; T_j = 25 \text{ }^\circ C$	-	0.4	0.7	nC
$Q_{GS}$	gate-source charge		-	0.1	-	nC
$Q_{GD}$	gate-drain charge		-	0.1	-	nC
$C_{iss}$	input capacitance	$V_{DS} = 10 V; f = 1 \text{ MHz}; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	21.3	-	pF
$C_{oss}$	output capacitance		-	5.4	-	pF
$C_{rss}$	reverse transfer capacitance		-	4.2	-	pF
$t_{d(on)}$	turn-on delay time		$V_{DS} = 10 V; I_D = 600 \text{ mA}; V_{GS} = 4.5 V; R_{G(ext)} = 6 \text{ } \Omega; T_j = 25 \text{ }^\circ C$	-	5.6	-
$t_r$	rise time	-		9.2	-	ns
$t_{d(off)}$	turn-off delay time	-		19	-	ns
$t_f$	fall time	-		51	-	ns
<b>Source-drain diode (per transistor)</b>						
$V_{SD}$	source-drain voltage	$I_S = 0.36 \text{ A}; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	0.8	1.2	V



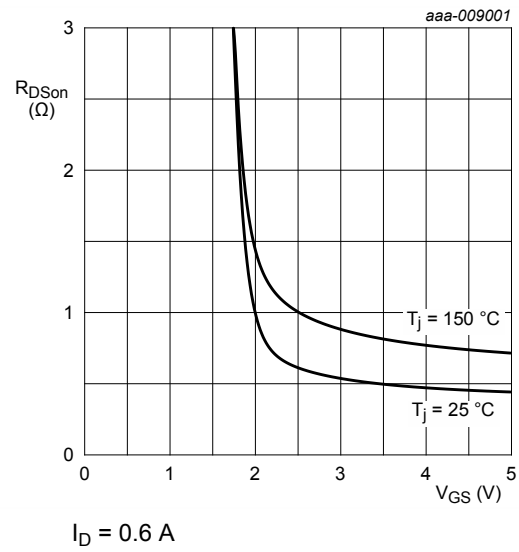
**Fig. 7. Output characteristics: drain current as a function of drain-source voltage; typical values**



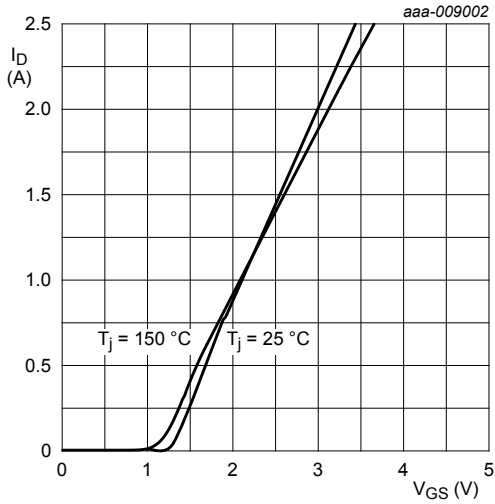
**Fig. 8. Sub-threshold drain current as a function of gate-source voltage**



**Fig. 9. Drain-source on-state resistance as a function of drain current; typical values**

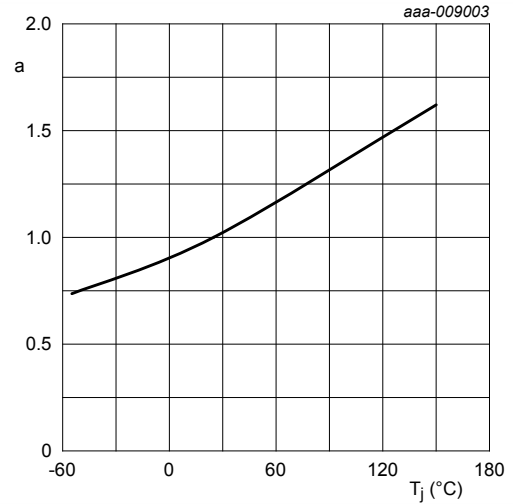


**Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values**



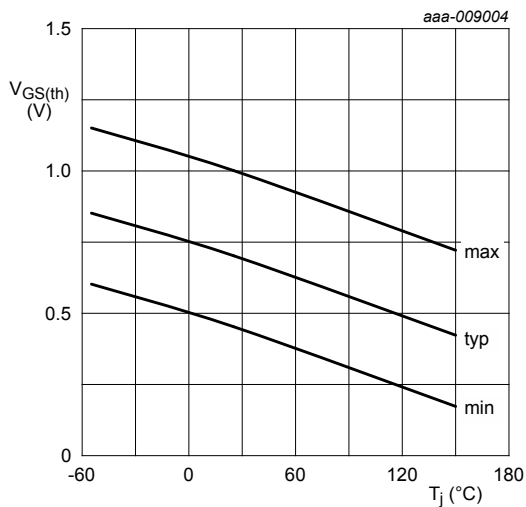
$$V_{DS} > I_D \times R_{DSon}$$

**Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values**



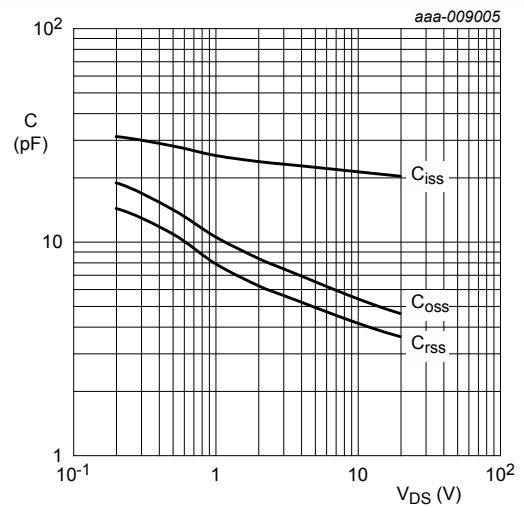
**Fig. 12. Normalized drain-source on-state resistance as a function of junction temperature; typical values**

$$a = \frac{R_{DSon}}{R_{DSon(25^\circ C)}}$$



$$I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$$

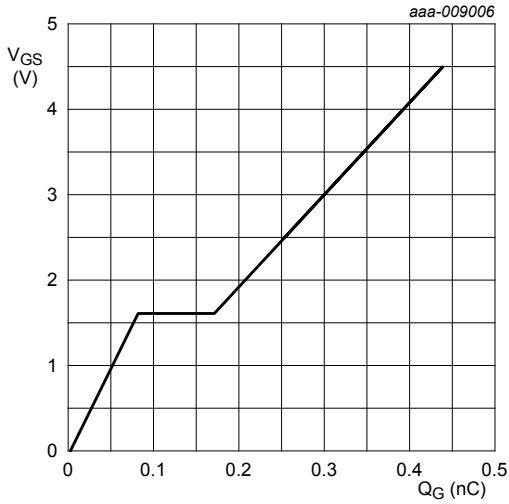
**Fig. 13. Gate-source threshold voltage as a function of junction temperature**



$$f = 1 \text{ MHz}; V_{GS} = 0 \text{ V}$$

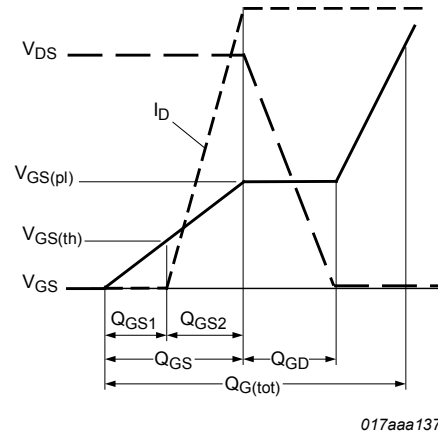
**Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**



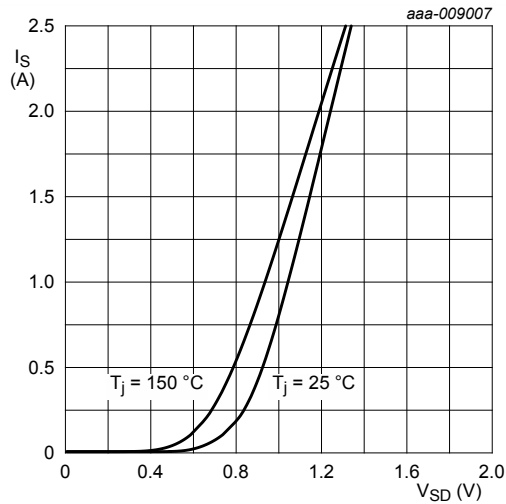


$I_D = 0.6 \text{ A}; V_{DS} = 10 \text{ V}; T_{amb} = 25 \text{ }^\circ\text{C}$

**Fig. 15. Gate-source voltage as a function of gate charge; typical values**



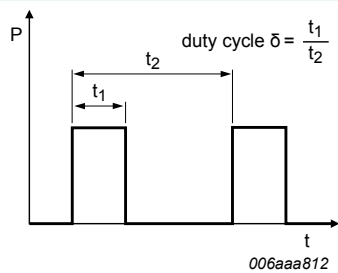
**Fig. 16. MOSFET transistor: Gate charge waveform definitions**



$V_{GS} = 0 \text{ V}$

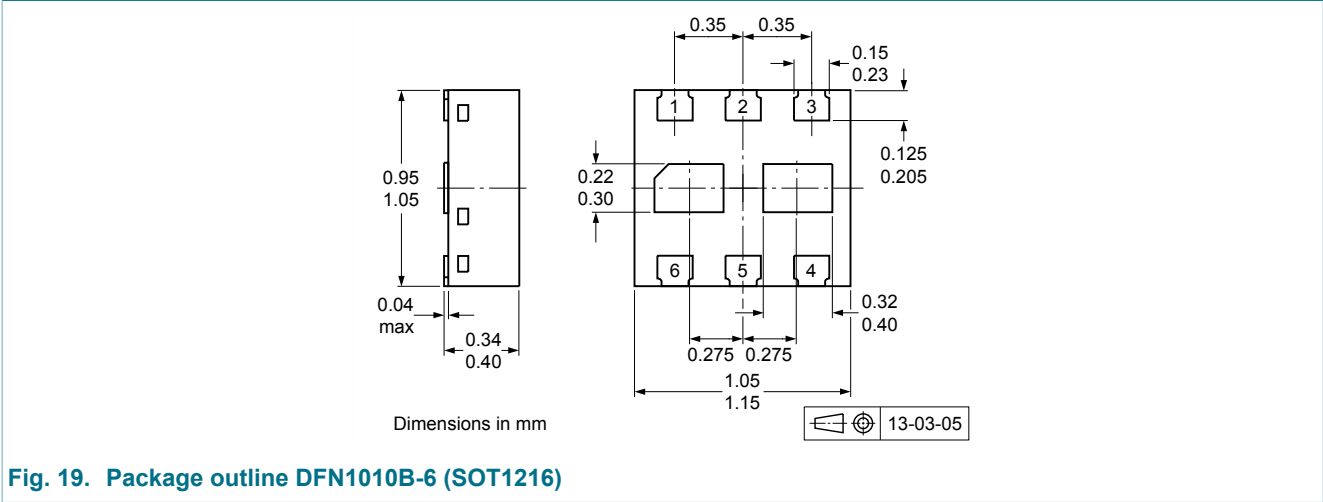
**Fig. 17. Source current as a function of source-drain voltage; typical values**

## 11. Test information



**Fig. 18. Duty cycle definition**

### 12. Package outline



### 13. Soldering

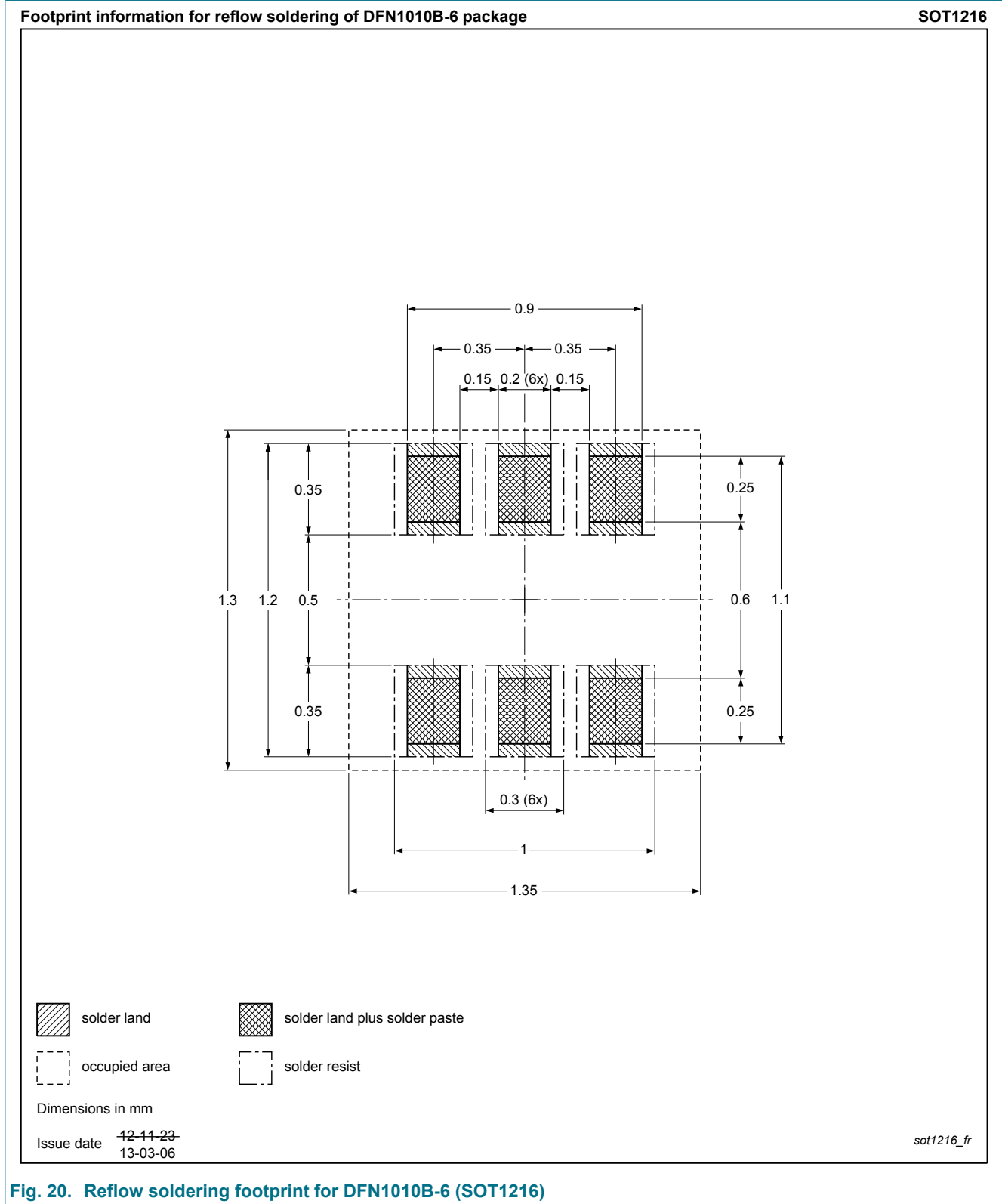


Fig. 20. Reflow soldering footprint for DFN1010B-6 (SOT1216)

## 14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMDXB600UNE v.1	20130916	Product data sheet	-	-

## 15. Legal information

### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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